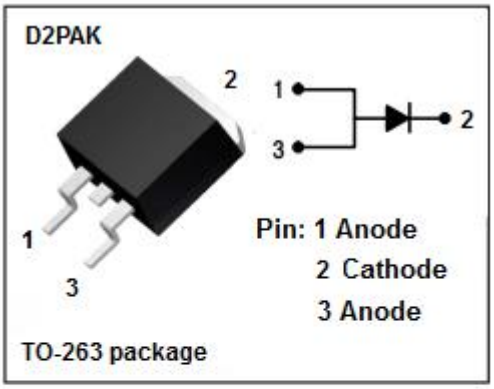
Schottky Barrier Rectifier

MBRB1645

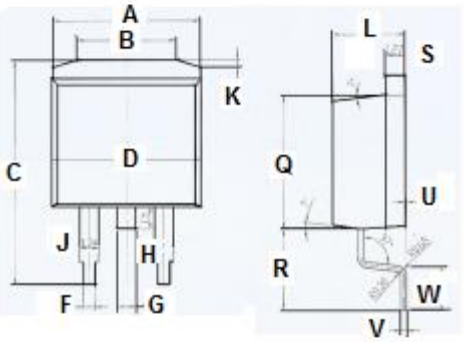


FEATURES

- Schottky barrier chip
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For use in high frequency rectifier of switching mode power supplies,freewheeling diodes,DC-to-DC converters or polarity protection application.



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RMS} V_R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	45	V
$I_{F(AV)}$	Average Rectified Forward Current	16	A
I_{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	150	A
T_J	Junction Temperature	-65~175	℃
T_{stg}	Storage Temperature Range	-65~175	℃

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.5	℃/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F=16A ; Tj=25℃		0.63	V
		I_F=16A ; Tj= 125℃		0.57	
I_R	Maximum Instantaneous Reverse Current	V_R= $V_{RWM;}$Tj= 25℃		200	uA
		V_R= $V_{RWM;}$Tj= 125℃		40	mA